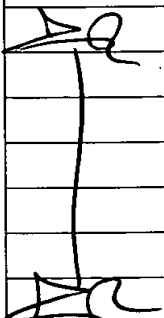
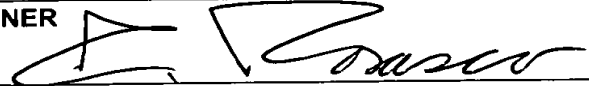

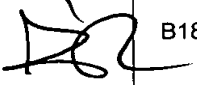


Form PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 039153-0450 (G1155)		SERIAL NO. 10/016,273		
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				APPLICANT Lukanc et al.				
				FILING DATE 12/11/2001		GROUP ART UNIT 1756		
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
	A1	6,410,193	6/25/2002	Stivers et al.	430	5	RECEIVED JUN 05 2003 1700	
	A2	6,013,399	1/11/00	Nguyen	430	5		
	A3	5,861,233	1/19/99	Sekine et al.	430	29/50		
	A4	5,780,187	7/14/98	Pierrat	430	5		
	A5	5,641,593	6/24/97	Watanabe et al.	430	5		
	A6	5,619,059	4/8/97	Li et al.	257	431		
	A7	5,328,784	7/12/1994	Fukuda	430	5		
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
	A8	EP 0 708 367 B1	14-01-1998	European			YES	NO
EXAMINER:  DATE CONSIDERED: 8/27/03								
* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.								

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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				APPLICANT Lukanc et al.		GROUP ART UNIT 1756	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	B9	T. BRUNNER ET AL., "170 nm gates fabricated by phase-shift mask and top anti-reflector process," 182/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-8.					
	B10	KURT RONSE ET AL., "Comparison of various phase shift strategies and application to 0.35 µm ASIC Designs," 2/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-15.					
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